

REMARKS

This paper is in response to the official action of June 15, 2005. Reconsideration is requested.

By the foregoing, claims 1, 10, and 16 are amended for clarity.

Reconsideration is requested.

Claim Rejections - 35 U.S.C. § 112

It is submitted that the amendment to claim 1 clarifies that claim, and reconsideration and withdrawal of the indefiniteness rejection of claims 1-9 are solicited.

Similarly, the amendments to claim 16 are directed to the alleged indefiniteness rejection of claims 16-18, and it is believed that the claims are clarified by the amendments.

Reconsideration and withdrawal of the indefiniteness rejection are believed proper, and are solicited.

Based on the indication of allowability of claims 1-9, allowance of this claims is solicited.

Claim Rejections - 35 U.S.C. § 103

Claims 10 and 12-16 have been rejected as obvious over Yu, Koh and Williams et al., and further in view of Kim et al. in the case of claim 13.

No basis for rejections of claim 11 has been stated.

Yu neither discloses nor suggests the features of the claimed invention. In particular, Yu fails to disclose or suggest the step of oxidizing the surface of the amorphous silicon layer to form a surface oxide film. Yu discloses oxidizing a polysilicon layer 22a by a thermal process, to form a silicon oxide layer 22b (col. 3, lines 26-30). However, the amorphous silicon (photoresist) layer of the present invention is partly oxidized, while the polysilicon layer of Yu is entirely oxidized. While the amorphous silicon layer of the present invention remains after oxidation, the polysilicon layer of Yu does not survive. Yu clearly

fails to disclose or suggest the feature of oxidizing the surface of the amorphous silicon layer to form a surface oxide film.

Further, Yu does not teach the step of etching the amorphous silicon film and the pad oxide film below the amorphous silicon film, thereby forming the isolation film, wherein the width of the top of the isolation film is widened up to an active region in the semiconductor substrate. Yu fails to disclose or suggest the formation the isolation film, wherein the width of the top of the isolation film is widened up to an active region in the semiconductor substrate.

Therefore, the applicant believes that the amended claims 10 -18 are patentable over the cited reference.

Should the examiner wish to discuss the foregoing or any matter of form in an effort to advance this application toward allowance, he is urged to telephone the undersigned at the indicated number.

Respectfully submitted,

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